

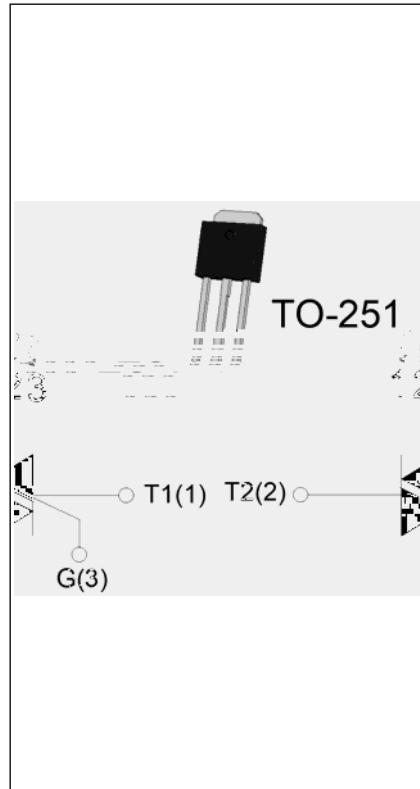


## T0610H-8H 6A TRIAC

Rev.A.1.0

## DESCRIPTION:

The T0610H-8H triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T0610H-8H provides a very high switching capability up to junction temperatures of 150°C. It can be driven directly through the MCU I/O port. From T2 terminals to external heatsink. Package TO-251 is RoHS compliant.



## MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	6	A
$V_{DRM}/V_{RRM}$	800	V
$I_{GT} / /$	10/10/10	mA

## ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	
Operating junction temperature range	$T_j$	-40-150	
Repetitive peak off-state voltage ( $T_j=25^\circ C$ )	$V_{DRM}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ C$ )	$V_{RRM}$	800	V
RMS on-state current ( $T_c = 119^\circ C$ )	$I_{T(RMS)}$	6	A
Non repetitive surge peak on-state current (full cycle, $t_p=20ms$ , $T_j=25^\circ C$ )	$I_{TSM}$	60	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6ms$ , $T_j=25^\circ C$ )		66	
$I^2t$ value for fusing ( $t_p=10ms$ , $T_j=25^\circ C$ )	$I^2t$	18	$A^2s$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100Hz$ , $T_j=150^\circ C$ )	$di/dt$	50	$A/\mu s$
Peak gate current ( $t_p=20\mu s$ , $T_j=150^\circ C$ )	$I_{GM}$	4	A
Average gate power dissipation ( $T_j=150^\circ C$ )	$P_{G(AV)}$	1	W

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Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25^\circ C$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	3	kV

ELECTRICAL CHARACTERISTICS ( $T_j=25^\circ C$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12V$ $R_L=33\Omega$	- -	MAX.	10	mA
$V_{GT}$		- -	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=150^\circ C$ $R_L=3.3K\Omega$	- -	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	-	MAX.	20	mA
				35	
$I_H$	$I_T=100mA$		MAX.	20	mA
$dV/dt$	$V_D=540V$ Gate Open $T_j=150^\circ C$		MIN.	150	V/ $\mu$ s
$(dI/dt)c$	$(dV/dt)c=20V/\mu s$ , $T_j=150^\circ C$		MIN.	1.5	A/ms
$t_{on}$	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25^\circ C$	TYP.	2.5	$\mu$ s	
$t_{off}$			25		

## STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=8.5A$	$t_p=380\mu s$	1.4	V
$V_{TO}$	Threshold voltage	$T_j=150^\circ C$	0.8	V
$R_D$	Dynamic resistance	$T_j=150^\circ C$	63	m

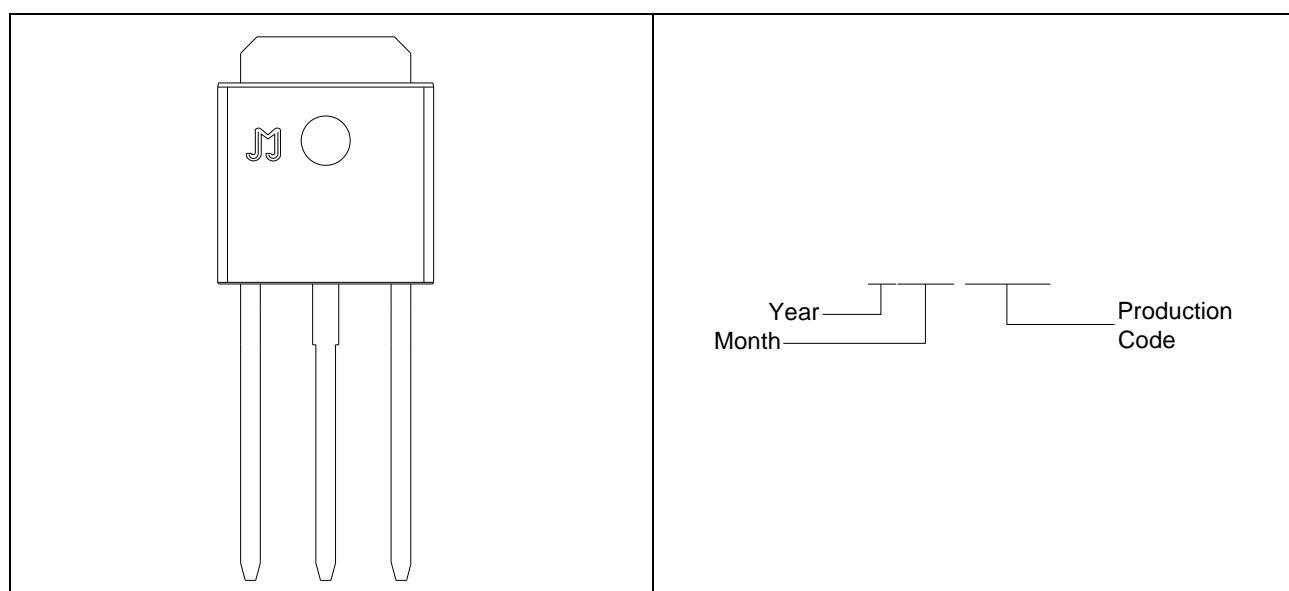
 $I_{DRM}$  $V_D=V_{DRM}$   $V_R=V_{RRM}$  $T_j=25^\circ C$ 

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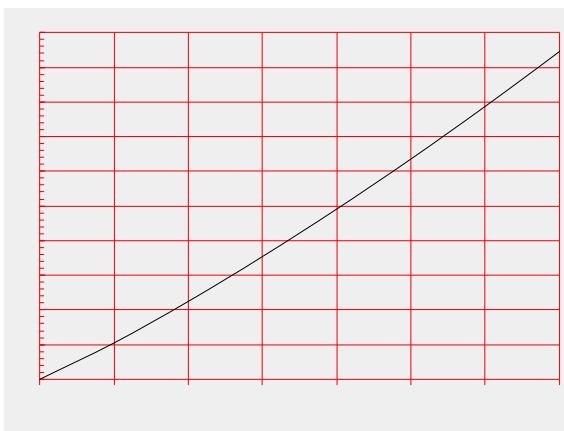
**ORDERING INFORMATION**

<b>T</b>	<b>06</b>	<b>10</b>	<b>H</b>	<b>-8</b>	<b>H</b>
Triacs					
	<u><math>I_T(\text{RMS})</math>:6A</u>				
		<u>10:IGT1-3 10mA</u>			
				<u>8:V<sub>DRM</sub> /V<sub>RRM</sub> 800V</u>	
					<u>High junction temperature</u>

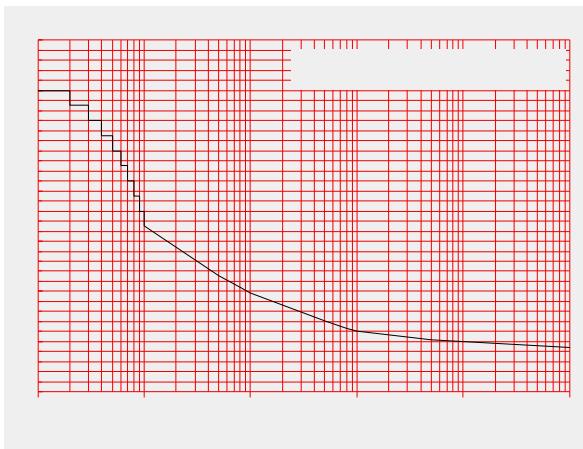
**MARKING**



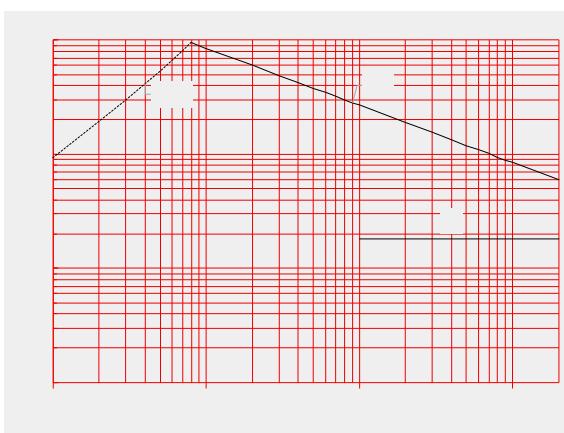
**FIG.1** Maximum power dissipation versus RMS on-state current



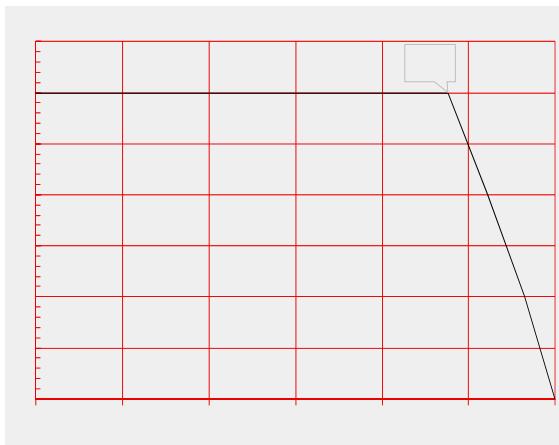
**FIG.3:** Surge peak on-state current versus number of cycles



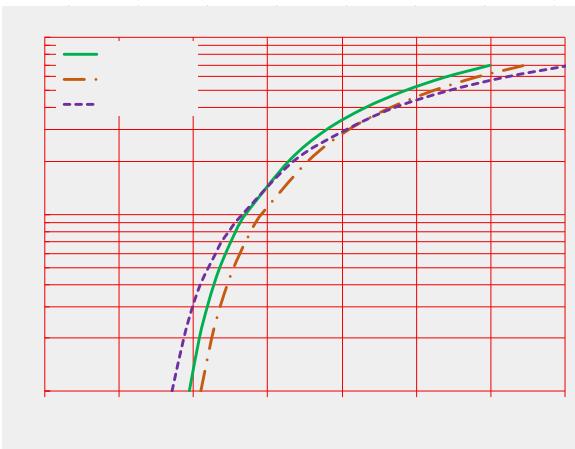
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $dI/dt < 50\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



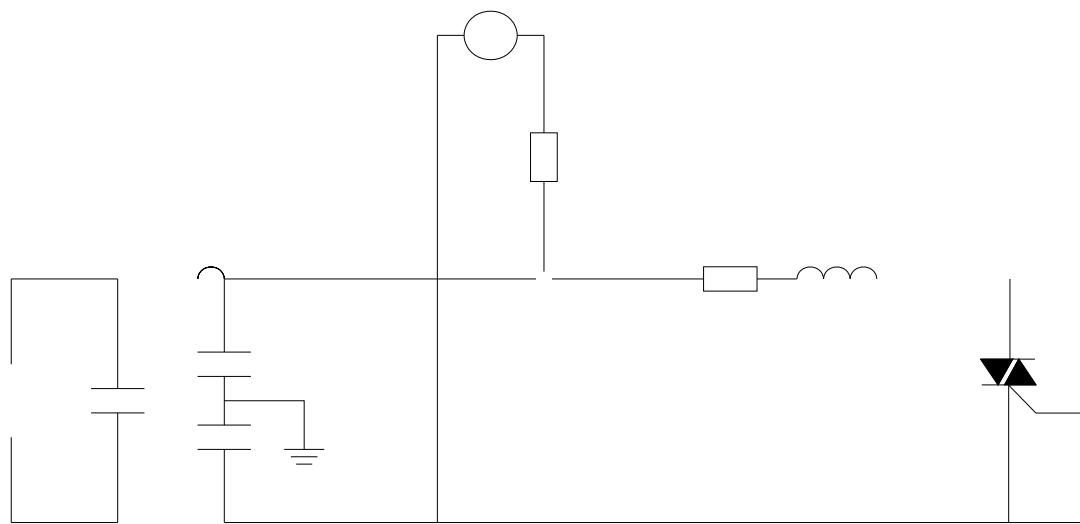
**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature



FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



**ORDERING INFORMATION**

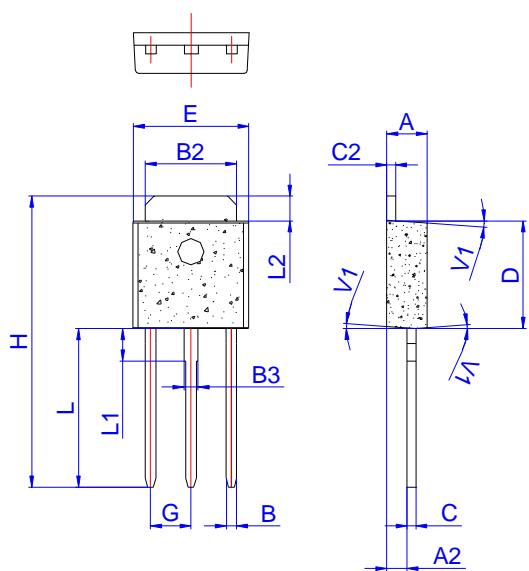
Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
<b>T0610H-8H</b>	<b>800</b>	<b>10</b>	<b>TO-251</b>	<b>80</b>	<b>Tube</b>

**Document Revision History**

Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated



## PACKAGE MECHANICAL DATA



Ref.	Dimensions			Inches			
	Millimeters	Min.	Typ.	Max.	Min.	Typ.	Max.
A							
A2							
B							
B2							



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